



# FDMC010N08C

## N-Channel Shielded Gate PowerTrench® MOSFET 80 V, 51 A, 10 mΩ

### Features

- Shielded Gate MOSFET Technology
- Max  $r_{DS(on)}$  = 10 mΩ at  $V_{GS}$  = 10 V,  $I_D$  = 16 A
- Max  $r_{DS(on)}$  = 25 mΩ at  $V_{GS}$  = 6 V,  $I_D$  = 8 A
- 50% lower  $Q_{rr}$  than other MOSFET suppliers
- Lowers switching noise/EMI
- MSL1 robust package design
- 100% UIL tested
- RoHS Compliant

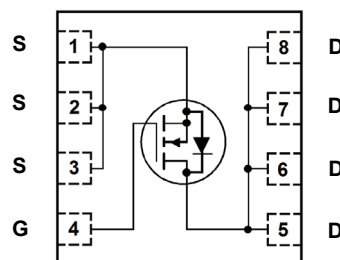
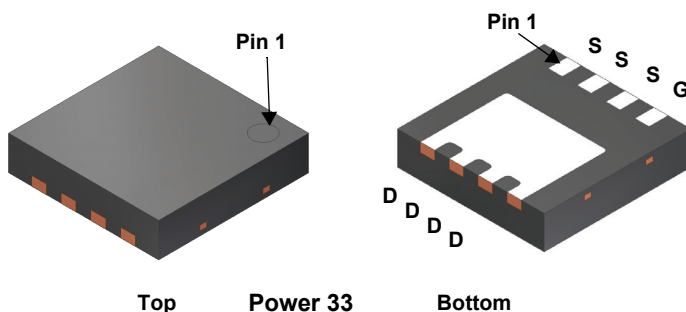


### General Description

This N-Channel MV MOSFET is produced using ON Semiconductor's advanced PowerTrench® process that incorporates Shielded Gate technology. This process has been optimized to minimise on-state resistance and yet maintain superior switching performance with best in class soft body diode.

### Applications

- Primary DC-DC MOSFET
- Synchronous Rectifier in DC-DC and AC-DC
- Motor Drive
- Solar



### MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain to Source Voltage	80	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current -Continuous $T_C = 25^\circ\text{C}$ (Note 5)	51	A
	-Continuous $T_C = 100^\circ\text{C}$ (Note 5)	32	
	-Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	11	
	-Pulsed (Note 4)	206	
$E_{AS}$	Single Pulse Avalanche Energy (Note 3)	96	mJ
$P_D$	Power Dissipation $T_C = 25^\circ\text{C}$	52	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	2.4	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	2.4	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	53	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC010N08C	FDMC010N08C	Power 33	13 "	12 mm	3000 units

**Electrical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off Characteristics**

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\ \mu\text{A}$ , $V_{GS} = 0\ \text{V}$	80			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , referenced to $25^\circ\text{C}$		75		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 64\ \text{V}$ , $V_{GS} = 0\ \text{V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\ \text{V}$ , $V_{DS} = 0\ \text{V}$			$\pm 100$	nA

**On Characteristics**

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 90\ \mu\text{A}$	2.0	2.9	4.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 90\ \mu\text{A}$ , referenced to $25^\circ\text{C}$		-8		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\ \text{V}$ , $I_D = 16\ \text{A}$		8.0	10	m $\Omega$
		$V_{GS} = 6\ \text{V}$ , $I_D = 8\ \text{A}$		12.3	25	
		$V_{GS} = 10\ \text{V}$ , $I_D = 16\ \text{A}$ , $T_J = 125^\circ\text{C}$		14	18	
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\ \text{V}$ , $I_D = 16\ \text{A}$		35		S

**Dynamic Characteristics**

$C_{iss}$	Input Capacitance	$V_{DS} = 40\ \text{V}$ , $V_{GS} = 0\ \text{V}$ , $f = 1\ \text{MHz}$		1070	1500	pF
$C_{oss}$	Output Capacitance			381	530	pF
$C_{rss}$	Reverse Transfer Capacitance			20	30	pF
$R_g$	Gate Resistance		0.1	0.4	0.7	$\Omega$

**Switching Characteristics**

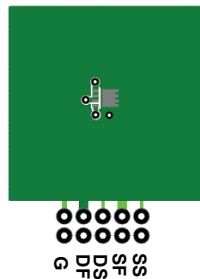
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 40\ \text{V}$ , $I_D = 16\ \text{A}$ , $V_{GS} = 10\ \text{V}$ , $R_{GEN} = 6\ \Omega$		9	19	ns
$t_r$	Rise Time			3	10	ns
$t_{d(off)}$	Turn-Off Delay Time			17	31	ns
$t_f$	Fall Time			5	10	ns
$Q_g$	Total Gate Charge	$V_{GS} = 0\ \text{V}$ to $10\ \text{V}$	$V_{DD} = 40\ \text{V}$ , $I_D = 16\ \text{A}$	15	22	nC
$Q_g$	Total Gate Charge	$V_{GS} = 0\ \text{V}$ to $6\ \text{V}$		10	14	nC
$Q_{gs}$	Gate to Source Charge			5		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			3		nC
$Q_{oss}$	Output Charge	$V_{DD} = 40\ \text{V}$ , $V_{GS} = 0\ \text{V}$		22.1		nC
$Q_{sync}$	Total Gate Charge Sync	$V_{DS} = 0\ \text{V}$ , $I_D = 16\ \text{A}$		13.3		nC

**Drain-Source Diode Characteristics**

$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\ \text{V}$ , $I_S = 2\ \text{A}$ (Note 2)		0.7	1.2	V
		$V_{GS} = 0\ \text{V}$ , $I_S = 16\ \text{A}$ (Note 2)		0.8	1.3	
$t_{rr}$	Reverse Recovery Time	$I_F = 8\ \text{A}$ , $di/dt = 300\ \text{A}/\mu\text{s}$		17	30	ns
$Q_{rr}$	Reverse Recovery Charge			20	33	nC
$t_{rr}$	Reverse Recovery Time	$I_F = 8\ \text{A}$ , $di/dt = 1000\ \text{A}/\mu\text{s}$		13	23	ns
$Q_{rr}$	Reverse Recovery Charge			45	73	nC

**Notes:**

1.  $R_{\theta JA}$  is determined with the device mounted on a 1 in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material.  $R_{\theta CA}$  is determined by the user's board design.



a.  $53^\circ\text{C}/\text{W}$  when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



b.  $125^\circ\text{C}/\text{W}$  when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300  $\mu\text{s}$ , Duty cycle < 2.0%.

3.  $E_{AS}$  of 96 mJ is based on starting  $T_J = 25^\circ\text{C}$ ,  $L = 3\ \text{mH}$ ,  $I_{AS} = 8\ \text{A}$ ,  $V_{DD} = 72\ \text{V}$ ,  $V_{GS} = 10\ \text{V}$ , 100% test at  $L = 0.1\ \text{mH}$ ,  $I_{AS} = 25\ \text{A}$ .

4. Pulsed  $I_d$  please refer to Fig 11 SOA graph for more details.

5. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

# Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted.

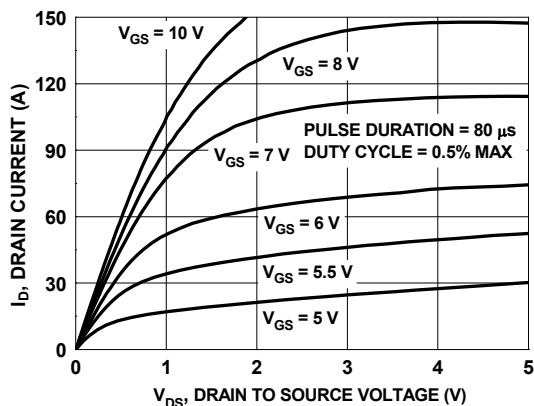


Figure 1. On Region Characteristics

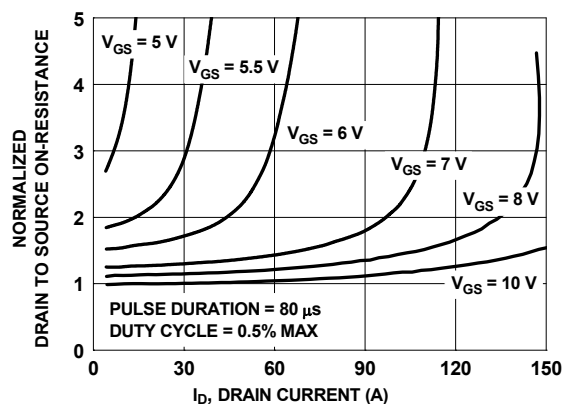


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

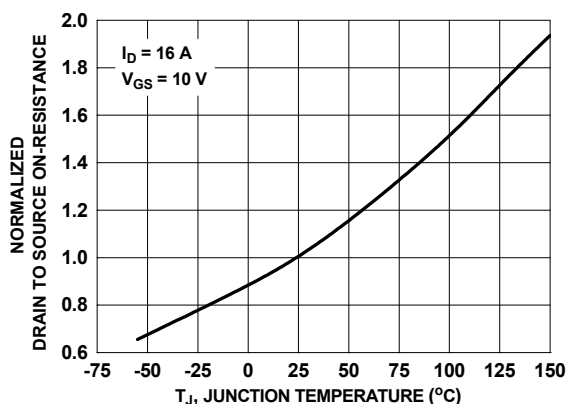


Figure 3. Normalized On Resistance vs. Junction Temperature

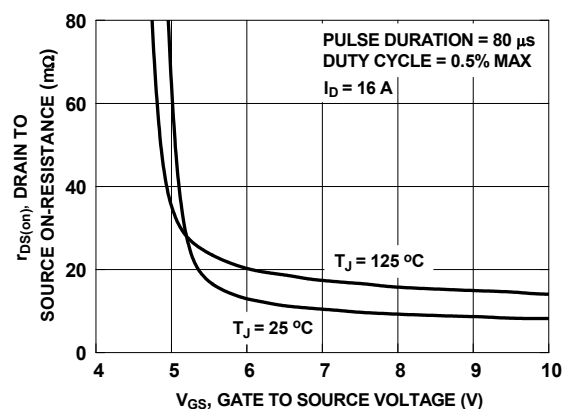


Figure 4. On-Resistance vs. Gate to Source Voltage

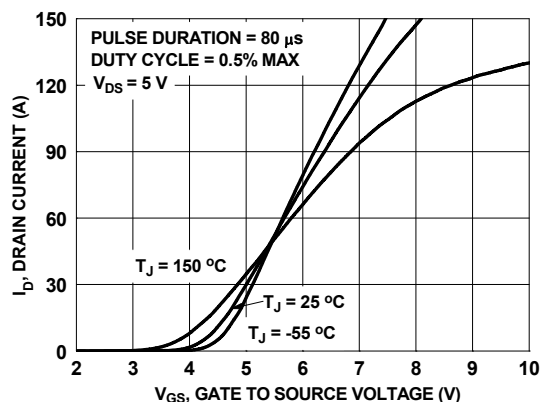


Figure 5. Transfer Characteristics

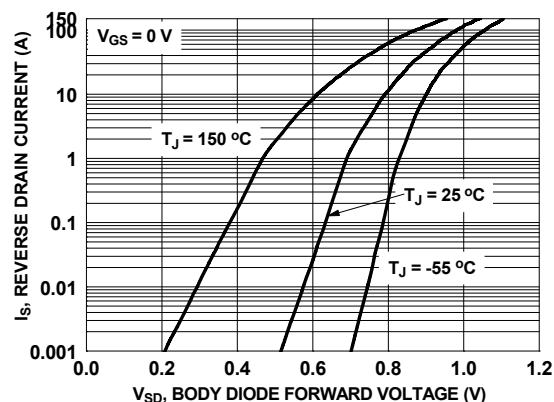
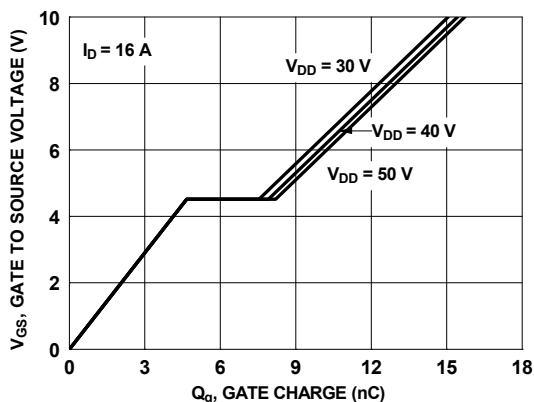
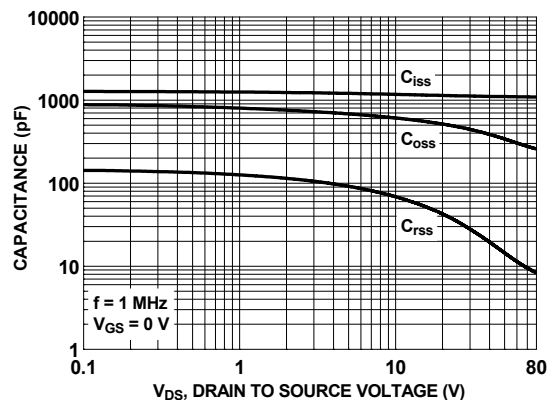


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

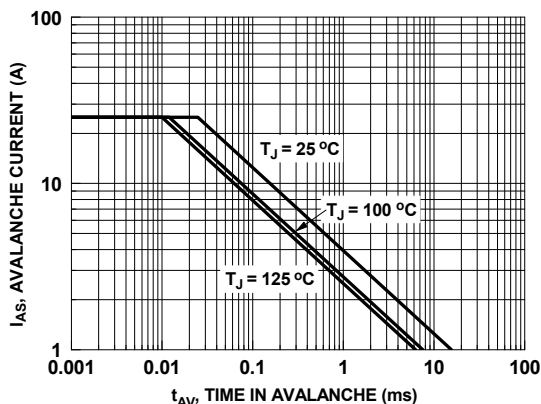
# **Typical Characteristics** $T_J = 25^\circ\text{C}$ unless otherwise noted.



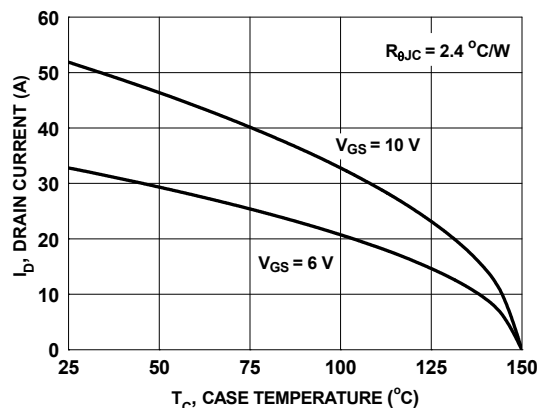
**Figure 7. Gate Charge Characteristics**



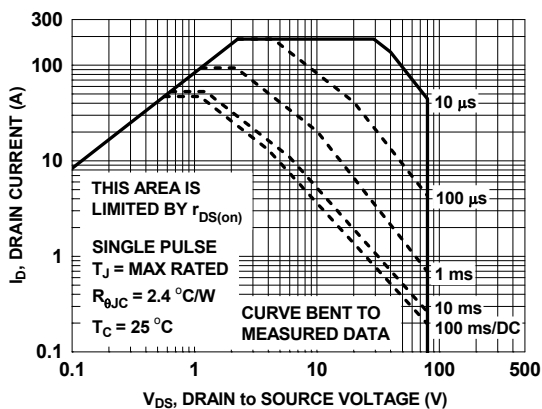
**Figure 8. Capacitance vs. Drain to Source Voltage**



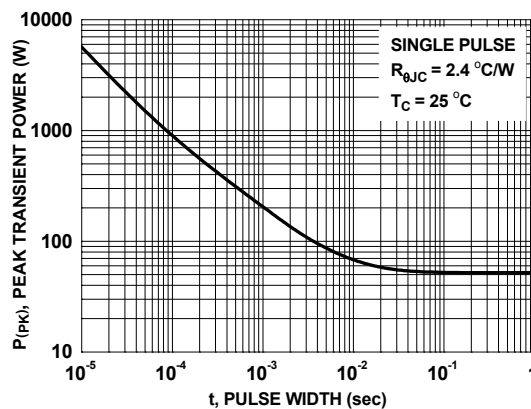
**Figure 9. Unclamped Inductive Switching Capability**



**Figure 10. Maximum Continuous Drain Current vs. Case Temperature**

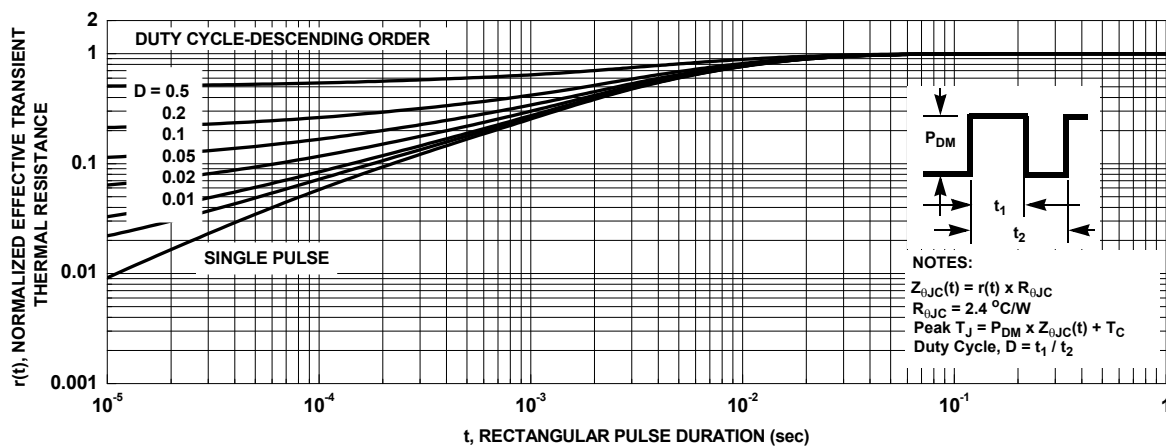


**Figure 11. Forward Bias Safe Operating Area**



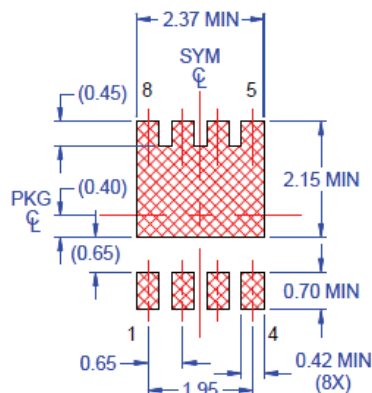
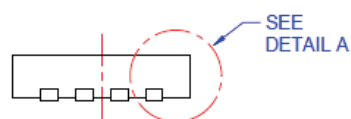
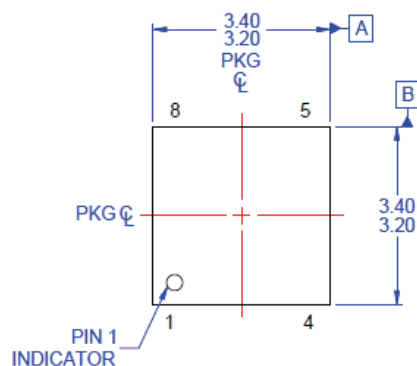
**Figure 12. Single Pulse Maximum Power Dissipation**

# **Typical Characteristics** $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted.

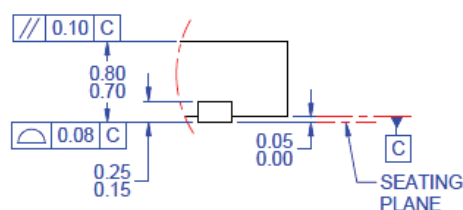
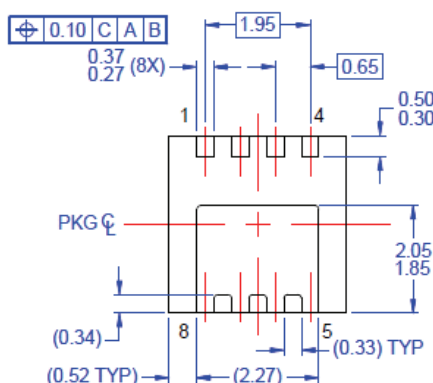


**Figure 13. Junction-to-Case Transient Thermal Response Curve**

# Dimensional Outline and Pad Layout



LAND PATTERN  
RECOMMENDATION



DETAIL A  
SCALE: 2X

## NOTES: UNLESS OTHERWISE SPECIFIED

- PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. BA, DATED OCTOBER 2002.
- ALL DIMENSIONS ARE IN MILLIMETERS.
- DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
- DRAWING FILE NAME: PQFN08HREV1

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